Peak gate current (t_p=20μs , T_j=125)	I_{GM}	10	A
Average gate power dissipation (T_j=125)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	V_D=12V R_L=33Ω	-	-	35	mA
V_{GT}		-	-	1	V
V_{GD}	V_D=V_{DRM} T_j=125 R_L=3.3kΩ	0.2	-	-	V
I_L	I_G=1.2I_{GT}	-	-	80	mA
I_H	I_T=500mA	-	-	70	mA
dV/dt	V_D=540V Gate Open T_j=125	1000	-	-	V/μs
t_{on}	I_G=40mA I_A=400mA I_R=40mA T_j=25	-	2	-	μs
t_{off}		-	60	-	

STATIC CHARACTERISTICS

Symbol **Parameter**

ORDERING INFORMATION

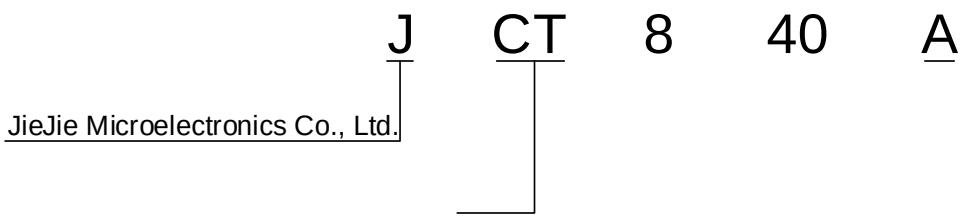


FIG.1: Maximum power dissipation versus RMS on-state current

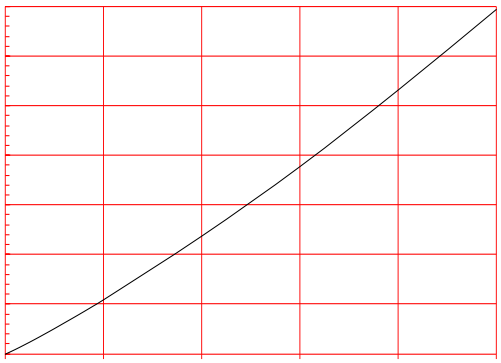
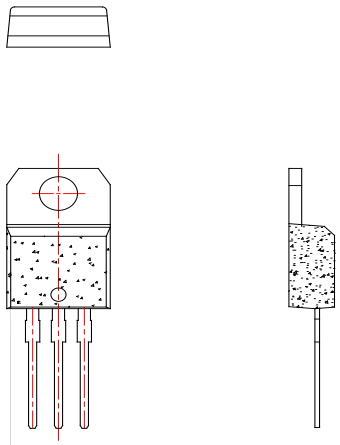


FIG.2: RMS on-state current versus case temperature

PACKAGE MECHANICAL DATA



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